Silicon PNP Power Transistors 2SA1043

DESCRIPTION

·With TO-3 package
·High transition frequency
·Excellent safe operating area

APPLICATIONS

·Power switching applications
·High frequency power amplifier
·Switching regulators
·DC-DC converters

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-30	A
P_C	Collector power dissipation	T_C=25□	150	W
T_j	Junction temperature		175	□
T_{stg}	Storage temperature		-55~200	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA ;I_B=0	-120			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-0.1mA ;I_E=0	-120			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-0.1mA ;I_C=0	-7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-15A; I_B=-1.5A			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-15A; I_B=-1.5A			-2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-120V; I_E=0			-50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-7V; I_C=0			-50	μA
h_{FE}	DC current gain	I_C=-3A ; V_{CE}=-5V	35		200	
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=-10V;f=1.0MHz		600		pF
f_T	Transition frequency	I_C=-2A ; V_{CE}=-10V		60		MHz

PACKAGE OUTLINE

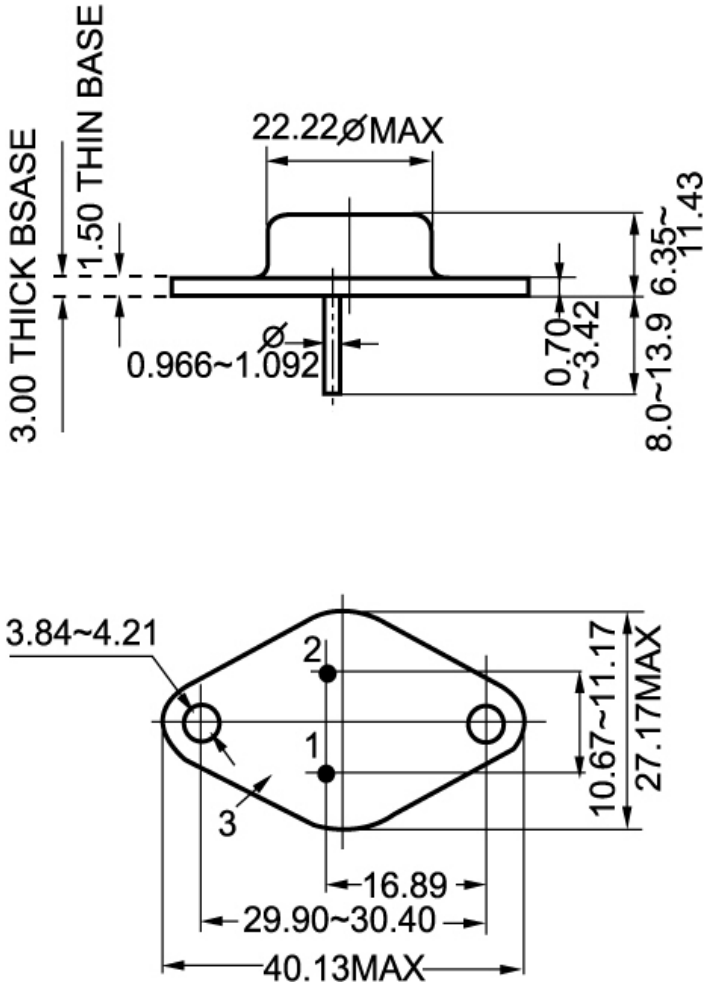

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)